

IN THE SPECIFICATION

Please replace the paragraph at page 2, lines 15-25, with the following rewritten paragraph:

Figure 9 is a view explaining bias conditions of a memory cell 10 in which hot electrons are written. Between a drain 12 and a source 14 of the memory cell, a voltage of about 5 V is applied, and a voltage of 10 V is applied to a gate 16 of the memory cell. This results in passing a large current 18 through a channel and drawing hot electrons 20 to a floating gate by an electric field between the gate and the channel, thereby achieving a write operation. If the memory cell is designed to represent "1" with an erased state, writing "0" in the memory cell is achieved by applying 5 V to the drain thereof and writing "1" in the memory cell is achieved by opening the drain thereof.

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